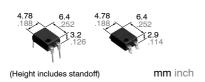




Load current greatly increased using next-generation MOSFET High Capacity 4-pin Type

GU PhotoMOS (AQY212GH)



FEATURES

- 1. Greatly increased load current.
- 2. Reinforced insulation 5,000 V type.
- 3. Greatly improved specs allow you to use this in place of mercury and mechanical relays.
- 4. Compact 4-pin DIP size.

TYPICAL APPLICATIONS

- Crime and fire prevention market (use in I/O for alarm and security devices, etc.)
- Amusement market
- Measuring instrument market (circuit testers, etc.)

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TYPES

Туре	Output rating*			Part	Packing quantity			
			Through hole terminal	Surface-mount terminal				
	Load voltage	Load current	Tube packing style		Tape and reel packing style			
					Picked from the 1/2-pin side	Picked from the 3/4-pin side	Tube	Tape and reel
AC/DC type	60 V	1.1 A	AQY212GH	AQY212GHA	AQY212GHAX	AQY212GHAZ	1 tube contains 100 pcs. 1 batch contains 1,000 pcs.	1,000 pcs.

^{*}Indicate the peak AC and DC values.

Note: For space reasons, the initial letters of the part number "AQY", the SMD terminal shape indicator "A" and the package style indicator "X" or "Z" are not marked on the relay.

RATING

1. Absolute maximum ratings (Ambient temperature: 25°C 77°F)

	Item	Symbol	AQY212GH(A)	Remarks
	LED forward current	lF	50 mA	
lanut	LED reverse voltage	VR	5 V	
Input	Peak forward current	I _{FP}	1 A	f = 100 Hz, Duty factor = 0.1%
	Power dissipation		75 mW	
	Load voltage (peak AC)	VL	60 V	
Output	Continuous load current (peak AC)	lι	1.1 A	
•	Peak load current	Ipeak	3.0 A	100ms (1 shot), V _L = DC
	Power dissipation	Pout	500 mW	
Total power dissipa	tion	P⊤	550 mW	
I/O isolation voltage)	Viso	5,000 V AC	
Tomporatura limita	Operating	Topr	-40°C to +85°C -40°F to +185°F	Non-condensing at low temperatures
Temperature limits	Storage	T _{stg}	-40°C to +100°C -40°F to +212°F	

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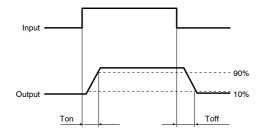
2. Electrical characteristics (Ambient temperature: 25°C 77°F)

Item			Symbol	AQY212GH(A)	Condition
	LED operate	Typical	Fon	1.1 mA	IL = 100mA
	current	Maximum		3 mA	IL = TOOMA
Innut	LED turn off	Minimum	Foff	0.3 mA	IL = 100mA
Input	current	Typical		1.0 mA	IL = TOOTHA
	LED dropout	Typical	VF	1.32 V (1.14 V at I _F = 5 mA)	I _F = 50 mA
	voltage	Maximum		1.5 V	IF = 30 IIIA
	On resistance	Typical	Ron	0.34 Ω	I _F = 5 mA I _L = Max.
Output	On resistance	Maximum		0.7 Ω	Within 1 s on time
·	Off state leakage current	Maximum	I _{Leak}	1 μΑ	I _F = 0 mA V _L = Max.
	T	Typical	Ton	1.3 ms	I _F = 5 mA
	Turn on time*	Maximum		5.0 ms	IL = 100 mA VL = 10 V
	T aff time a *	Typical	Toff	0.1 ms	I _F = 5 mA
Transfer characteristics	Turn off time*	Maximum		0.5 ms	IL = 100 mA VL = 10 V
		Typical	Ciso	0.8 pF	f = 1 MHz
	I/O capacitance	Maximum		1.5 pF	V _B = 0 V
	Initial I/O isolation resistance	Minimum	Riso	1,000 MΩ	500 V DC

Notes: 1. Type of connection

2. Recommendable LED forward current I_F = 5 to 10 mA.

*Turn on/Turn off time

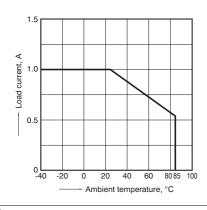


- **Dimensions**
- **Schematic and Wiring Diagrams**
- **Cautions for Use**

REFERENCE DATA

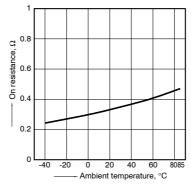
1. Load current vs. ambient temperature characteristics

Allowable ambient temperature: -40° C to $+85^{\circ}$ C -40° F to $+185^{\circ}$ F



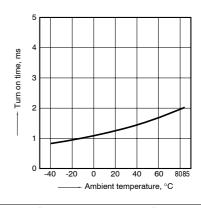
2. On resistance vs. ambient temperature characteristics

Measured portion: between terminals 3 and 4; LED current: 5 mA; Load voltage: Max. (DC) Continuous load current: Max.(DC)



3. Turn on time vs. ambient temperature characteristics

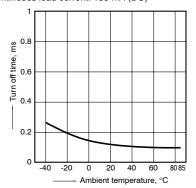
LED current: 5 mA; Load voltage: 10 V (DC); Continuous load current: 100 mA (DC)



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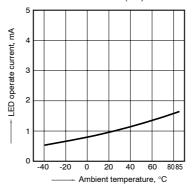
4. Turn off time vs. ambient temperature characteristics

LED current: 5 mA; Load voltage: 10 V (DC); Continuous load current: 100 mA (DC)



5. LED operate current vs. ambient temperature characteristics Load voltage: 10 V (DC);

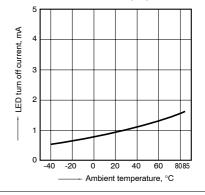
Continuous load current: 100mA (DC)



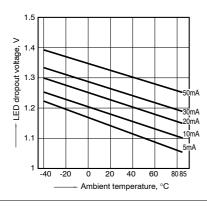
6. LED turn off current vs. ambient temperature characteristics

Load voltage: 10 V (DC);

Continuous load current: 100mA (DC)

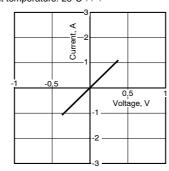


7. LED dropout voltage vs. ambient temperature characteristics LED current: 5 to 50 mA



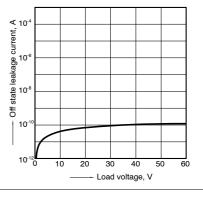
8. Current vs. voltage characteristics of output at MOS portion

Measured portion: between terminals 3 and 4; Ambient temperature: 25°C 77°F



Off state leakage current vs. load voltage characteristics

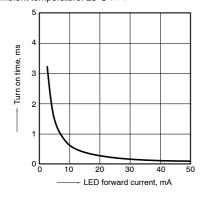
Measured portion: between terminals 3 and 4; Ambient temperature: 25°C 77°F



10. Turn on time vs. LED forward current characteristics

Measured portion: between terminals 3 and 4; Load voltage: 10 V (DC);

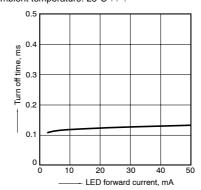
Continuous load current: 100 mA (DC); Ambient temperature: 25°C 77°F



Turn off time vs. LED forward current characteristics

Measured portion: between terminals 3 and 4; Load voltage: 10 V (DC);

Continuous load current: 100 mA (DC); Ambient temperature: 25°C 77°F



12. Output capacitance vs. applied voltage characteristics

Measured portion: between terminals 3 and 4;

Frequency: 1 MHz;

Ambient temperature: 25°C 77°F

